

MA2Q739

Silicon epitaxial planar type

For high-frequency rectification

■ Features

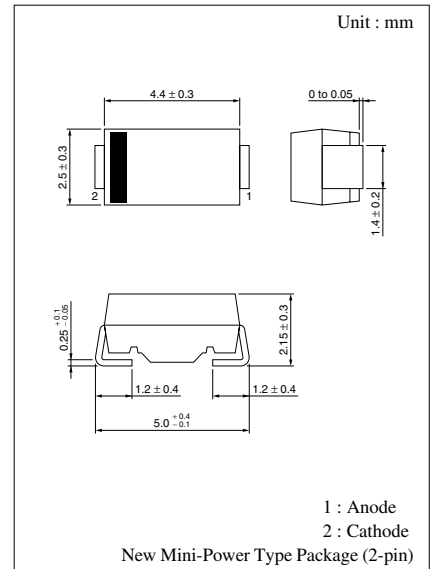
- Forward current (average) $I_{F(AV)}$: 0.7 A type
- Reverse voltage (DC value) V_R : 90 V
- Allowing automatic insertion with the emboss taping

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	90	V
Repetitive peak reverse voltage	V_{RRM}	90	V
Average forward current* ¹	$I_{F(AV)}$	0.7	A
Non-repetitive peak forward surge current* ²	I_{FSM}	10	A
Junction temperature	T_j	-40 to +125	$^\circ\text{C}$
Storage temperature	T_{stg}	-40 to +125	$^\circ\text{C}$

Note) *1 : With a printed-circuit board

*2 : The peak-to-peak value in one cycle of 50 Hz sine-wave
(non-repetitive)



Marking Symbol: PE

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 90\text{ V}$			1	mA
Forward voltage (DC)	V_F	$I_F = 0.7\text{ A}$			0.8	V
Terminal capacitance	C_t	$V_R = 10\text{ V}, f = 1\text{ MHz}$		50		pF
Reverse recovery time*	t_{rr}	$I_F = I_R = 100\text{ mA}$ $I_{rr} = 10\text{ mA}, R_L = 100\ \Omega$			100	ns

Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.

2. Rated input/output frequency: 10 MHz

3. *: t_{rr} measuring instrument

